

General Purpose Transistors

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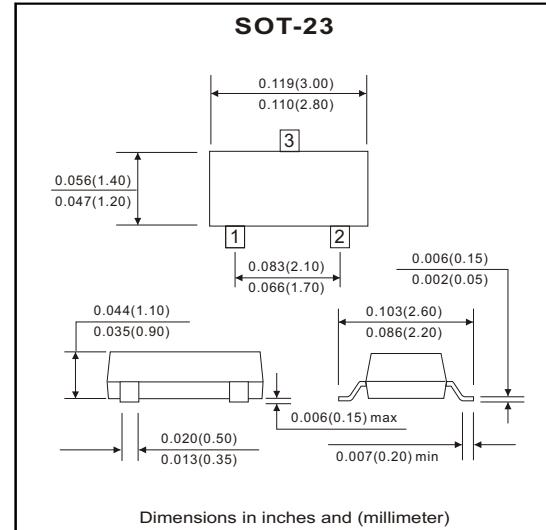
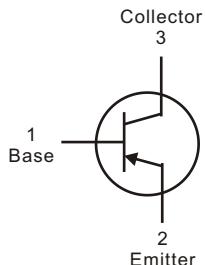
MMBT4403-G (PNP) RoHS Device



Features

- Switching transistor.

Marking: 2T



Maximum Ratings (at Ta=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-Base voltage	V _{CBO}	-40	V
Collector-Emitter voltage	V _{CEO}	-40	V
Emitter-Base voltage	V _{EBO}	-5	V
Collector current-continuous	I _c	-0.6	A
Collector power dissipation	P _c	300	mW
Junction temperature	T _j	150	°C
Storage temperature range	T _{STG}	-55 to +150	°C

Electrical Characteristics (at Ta=25°C unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ.	Max	Unit
Collector-Base breakdown voltage	V _{(BR)CBO}	I _c =-100μA, I _e =0	-40			V
Collector-Emitter breakdown voltage	V _{(BR)CEO}	I _c =-1mA, I _b =0	-40			V
Emitter-Base breakdown voltage	V _{(BR)EBO}	I _e =-100μA, I _c =0	-5			V
Collector cut-off current	I _{cbo}	V _{CB} =-35V, I _e =0			-0.1	μA
Collector cut-off current	I _{ceo}	V _{CE} =-35V, I _b =0			-0.1	μA
Emitter cut-off current	I _{ebo}	V _{EB} =-4V, I _c =0			-0.1	μA
DC current gain	h _{FE}	V _{CE} =-2V, I _c =-150mA	100		300	
Collector-Emitter saturation voltage	V _{CE(SAT)}	I _c =-150mA, I _b =-15mA			-0.4	V
Base-Emitter saturation voltage	V _{BE(SAT)}	I _c =-150mA, I _b =-15mA			-0.95	V
Transition frequency	f _T	V _{CE} =-10V, I _c =-20mA f=100MHz	200			MHz

REV:A

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RATING AND CHARACTERISTIC CURVES (MMBT4403-G)

Fig.1 Max. Power Dissipation vs. Ambient Temperature

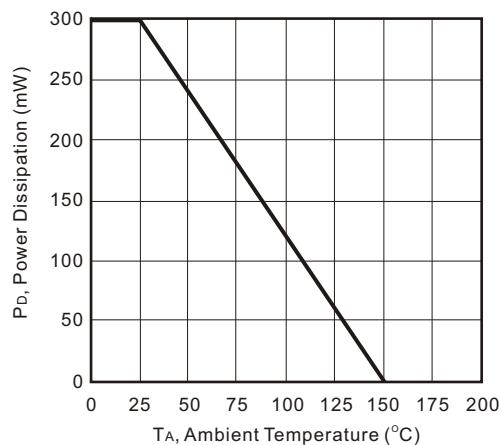


Fig. 2 Typical DC Current Gain vs. Collector Current

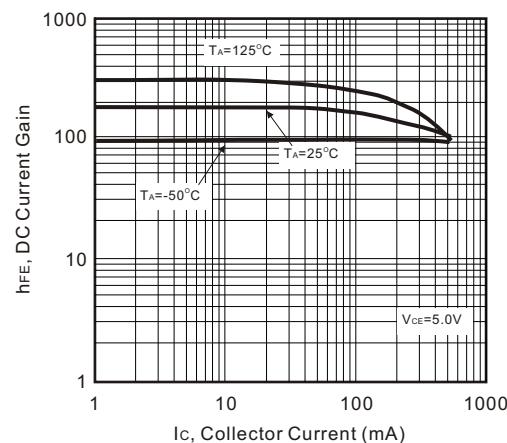


Fig. 3 Typical Capacitance

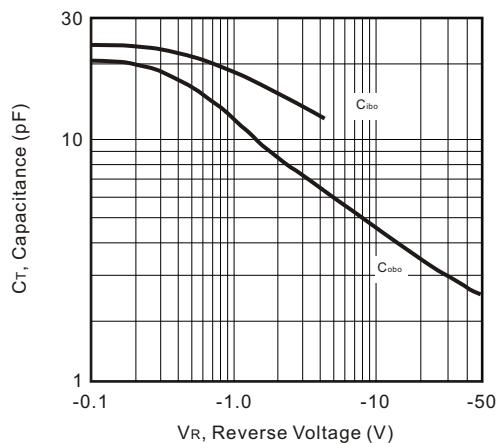


Fig. 4 Typical Collector Saturation Region

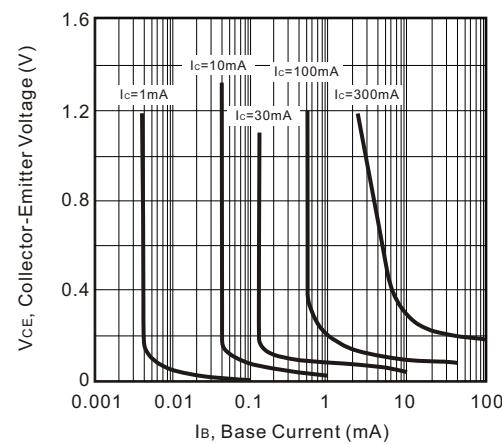


Fig. 5 Collector-Emitter Saturation Voltage vs. Collector Current

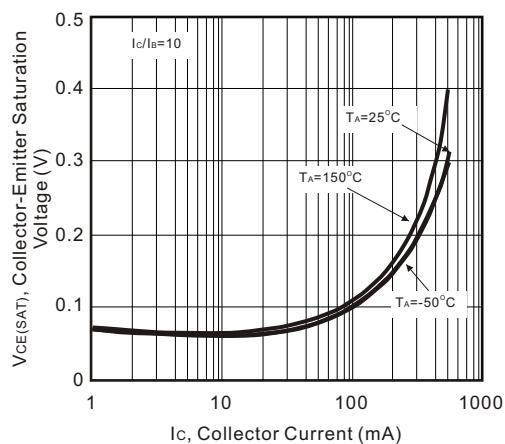


Fig. 6 Base-Emitter Voltage vs. Collector Current

